

METHOD OF FORMING A SEMI-INSULATING REGION

Abstract

A semiconductor substrate is provided, and at least one first mask is formed above the semiconductor substrate. The first mask blocks at least one semi-insulating region. A second mask is thereafter formed on a surface of the semiconductor substrate. The second mask covers the semi-insulating region. The semi-insulating region is implanted with a high energy beam of particles by utilizing the second mask and the first mask as particle hindering masks. Finally, the second mask is removed.